Superconductivity of $M_I(M_{II0.5}, Si_{0.5})_2$ (M_I =Sr and Ba, M_{II} =Al and Ga), ternary silicides with the AlB₂-type structure

Motoharu Imai, Kenji Nishida, Takashi Kimura, Hideaki Kitazawa, Hideki Abe National Institute for Materials Science 1-2-1 Sengen, Tsukuba, Ibaraki 305-0047, JAPAN Hijiri Kito National Institute of Advanced Industrial Science and Technology 1-1-1 Umezono, Tsukuba, Ibaraki 305-8568, JAPAN Kenji Yoshii Japan Atomic Energy Research Institute Mikazuki, Hyogo 679-5148 JAPAN

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Ternary silicides $M_I(M_{II0.5}, Si_{0.5})_2$ (M_I =Sr and Ba, M_{II} =Al and Ga) were prepared by Ar arc melting. Powder X-ray diffraction indicates that they have the AlB₂-type structure, in which Si and M_{II} atoms are arranged in honeycomb layers and M_I atoms are intercalated between them. Electrical resistivity and dc magnetization measurements revealed that Sr(Al_{0.5}, Si_{0.5})₂ is superconductive, with a critical temperature for superconductivity (T_C) of 4.2 K, while Ba(Al_{0.5}, Si_{0.5})₂ is not at temperatures ranging above 2.0 K. Sr(Ga_{0.5}, Si_{0.5})₂ and Ba(Ga_{0.5}, Si_{0.5})₂ are also superconductors, with T_C s of 5.1 and 3.3 K, respectively.

Keywords: superconductivity, silicide, AlB₂-type structure, Sr(Al, Si)₂ PACS: 74.10.+v, 61.66.Fn, 74.70.Ad

Corresponding Author: Motoharu IMAI National Institute for Materials Science 1-2-1 Sengen, Tsukuba, IBARAKI 305-0047, JAPAN E-mail:IMAI.Motoharu@nims.go.jp Tel: +81-298-59-2814, Fax: +81-298-59-2801

1. Introduction

Superconductivity at 39 K was recently reported with an intermetallic compound, MgB₂ [1]. Magnesium diboride has the AlB₂-type (C32-type) structure and, therefore, related compounds are attracting attention because of their potential as new superconductors. The discovery and study of new superconductors with the AlB₂-type structure are relevant to our understanding of the origin of the superconductivity of MgB₂. Silicides, as well as borides, also contain compounds with the AlB₂-type structure or a structure related to it.

Of binary silicides, ThSi₂ [2], USi₂ [3], and several rare-earth metal disilicides [4, 5] are known to have an AlB₂-type structure. Among them, β -ThSi₂ is known to be a superconductor with a critical temperature $T_{\rm C}$ of 2.41 K [6]. A high-pressure phase of CaSi₂, which appears above 16 GPa, has an AlB₂-like structure in which Si atoms form slightly corrugated honeycomb layers [7]. This phase of CaSi₂ is superconductive, with a $T_{\rm C}$ of 14 K at such pressures [8], while the ambient phase is not [9]. This high-pressure phase cannot be quenched at ambient conditions.

Recently, ternary silicides $M_{AE}(Ga_x, Si_{1-x})_2$ ($M_{AE}=Ca, Sr, and Ba$) have been reported to have the AlB₂-type structure and to be superconductors with a T_C ranging from 3.3 to 3.9 K [10, 11]. Furthermore, a ternary silicide, Ca(Al_{0.5}, Si_{0.5})₂, which has the AlB₂-type structure, has been reported to be a superconductor with a T_C of 7.7 K [12]. Ternary silicides Sr(Al_x, Si_{1-x})₂ and Ba(Al_x, Si_{1-x})₂ have been reported to have the AlB₂-type structure [13-16], though their electrical properties have not been examined yet. It would be interesting to examine whether the Sr(Al_x, Si_{1-x})₂ and Ba(Al_x, Si_{1-x})₂ show superconductivity, as $M_{AE}(Ga_x, Si_{1-x})_2$ and Ca(Al_{0.5}, Si_{0.5})₂ do.

Here, we report the synthesis of ternary silicides $Sr(Al_{0.5}, Si_{0.5})_2$ and $Ba(Al_{0.5}, Si_{0.5})_2$ and demonstrate that $Sr(Al_{0.5}, Si_{0.5})_2$ is a superconductor. We also investigated $Sr(Ga_{0.5}, Si_{0.5})_2$ and $Ba(Ga_{0.5}, Si_{0.5})_2$ for comparison.

2. Experimental

The samples were prepared by Ar arc melting of 1 : 1 : 1 stoichiometric mixtures of M_I (M_I= Sr and Ba, nominal purity 99.5 %), M_{II} (M_{II}=Al and Ga, nominal purity 99.999 %), and Si (nominal purity 99.9999 %). In the following, ARC-M_IM_{II} denotes the sample prepared by Ar arc melting of 1 : 1 : 1 stoichiometric mixtures of M_I, M_{II}, and Si. Their chemical compositions were determined using electron probe microanalysis (EPMA). The samples for EPMA were prepared by polishing with an oil-based diamond slurry to avoid a reaction with water. The structure of the silicides was examined using a powder X-ray diffraction method. Electrical resistivity was measured by means of the four-probe method at temperatures ranging from 2 to 290 K. Since ARC-SrAl and ARC-BaAl were slightly sensitive to moisture in air, they were covered with insulating varnish (General Electric, 7031) after spark-bonding of Au wires. dc magnetization was measured using a SQUID magnetometer at temperatures ranging from 2 to 12 K.

3. Results

Map analysis by EPMA shows that all the samples consist of almost a single phase, though they contain small amounts of precipitates. Table I lists the average chemical

composition of the main phase determined with EPMA, which confirms that the $M_I(M_{II0.5}Si_{0.5})_2$ phase is the main one in all the samples. A small amount of oxygen was detected in ARC-BaGa. This would be, however, due to the surface oxidization of samples because the amount of oxygen detected was small and it was also detected in the precipitates.

Figure 1 shows the powder X-ray diffraction patterns of the samples and calculated diffraction patterns for the $M_I(M_{II0.5}Si_{0.5})_2$ phase with the AlB₂-type structure. For the calculation, we assumed that the compound $M_I(M_{II0.5}, Si_{0.5})_2$ would have the AlB₂-type structure with the observed lattice constants described below, in which the 2d site is chemically disordered with occupation probabilities of 0.5 for the element M_{II} and 0.5 for Si. The major observed reflections are reproduced well by the assumed structure, as shown in Fig. 1. These results indicate that the $M_I(M_{II0.5}Si_{0.5})_2$ phase has the AlB₂-type structure.

Their lattice constants are listed in Table II, together with those of $Ca(Al_{0.5}, Si_{0.5})_2$ [12] and $Ca(Ga_{0.5}, Si_{0.5})_2$ [11]. When the alkaline-earth elements are changed, the lattice constants change anisotropically: the lattice constant *a* increases by 2.5 % for M_I(Al_{0.5}, Si_{0.5})₂ and by 3.3 % for M_I(Ga_{0.5}, Si_{0.5})₂, while the lattice constant *c* increases by 16.9 % for M_I(Al_{0.5}, Si_{0.5})₂ and 14.9 % for M_I(Ga_{0.5}, Si_{0.5})₂ when the alkaline-earth elements are changed in the sequence Ca, Sr, and Ba.

Figures 2 and 3show the electrical resistivity of $M_I(Al_{0.5}, Si_{0.5})_2$ and $M_I(Ga_{0.5}, Si_{0.5})_2$ as a function of the temperature, respectively. The resistivity starts to decrease at temperature T_C^{ONSET} and becomes negligibly small at temperature T_C^{ZERO} in all the samples except for Ba(Al_{0.5}, Si_{0.5})_2. Table III lists T_C^{ONSET} and T_C^{ZERO} together with those of related materials. The resistivity of Ba(Al_{0.5}, Si_{0.5})_2 decreases continuously with decreasing the temperature down to 2 K, the lowest temperature of this experiment. These results suggest that the silicides $M_I(M_{II0.5}, Si_{0.5})_2$ become superconductive at T_C^{ZERO} except for Ba(Al_{0.5}, Si_{0.5})_2.

Figure 4 shows the dc magnetization *M* of $M_I(M_{II0.5}, Si_{0.5})_2$ except for $Ba(Al_{0.5}, Si_{0.5})_2$ in a field *H* as a function of the temperature. The triangles and circles show data obtained in zero-field cooling (ZFC) and those in field cooling (FC), respectively. The samples show a Meissner effect (flux exclusion) below a temperature T_C^{MEIS} in FC, which confirms the presence of a superconducting phase below the temperature, as indicated by the resistivity measurements. Table III also lists T_C^{MEIS} , the magnetic shielding fraction in ZFC, and the flux exclusion in FC at 2.0 K. These indicate that the superconductivity is a bulk effect. On this basis, we conclude that ternary silicides $M_I(M_{II0.5}, Si_{0.5})_2$ are superconductors with the AlB₂-type structure, except for Ba(Al_{0.5}, Si_{0.5})₂. Therefore, it is revealed that six ternary M_{AE} -M_{II}-Si systems (M_{AE} =Ca, Sr, and Ba, M_{II} =Al and Ga) have compounds with the AlB₂type structure, and the compounds in the systems are superconductive, except for that in the Ba-Al-Si system.

4. Discussion

In the silicides with the same third element M_{II} , the T_C depends on the choice of M_{AE} . In the silicides $M_{AE}(Al_{0.5}, Si_{0.5})_2$, the T_C decreases when the element M_{AE} is changed from Ca into Sr and finally becomes lower than 2 K, the lowest temperature in this study, when the

element M_{AE} is Ba. On the other hand, in the silicides $M_{AE}(Ga_{0.5}, Si_{0.5})_2$, the T_C becomes the highest when the element M_{AE} is Sr.

In the Bardeen-Cooper-Schrieffer theory, the $T_{\rm C}$ is estimated as

 $T_{\rm C}=1.13\Theta_{\rm D}\exp(-1/N(E_{\rm F})V),$

where Θ_D is the Debye frequency, $N(E_F)$ is the density of states at the Fermi level, and V is the average electron pairing interaction [17]. In the silicides $M_{AE}(B_{0.5}, Si_{0.5})_2$, the Debye temperature is expected to be the same because the composition of honeycomb layers is the same in the three compounds. Therefore, the different $T_{\rm C}$ in $M_{\rm AE}(M_{\rm H0.5}, Si_{0.5})_2$ would be attributed to the change in $N(E_{\rm F})$ under the assumption that V is independent of the choice of M_{AE} . The change of the element M_{AE} affects $N(E_F)$ in two ways. One is the effect on the Fermi energy. When the element M_{AE} is changed in the sequence Ca, Sr, and Ba, the volume of the unit cell increases, as shown in Table II, and the valence electron density decreases. Consequently, the Fermi energy decreases in the sequence because the Fermi energy is proportional to 2/3 the power of the valence electron density. For instance, the difference in the Fermi energy between Ca(Al_{0.5}, Si_{0.5})₂ and Ba(Al_{0.5}, Si_{0.5})₂ is roughly estimated to be 13 %. The other is an effect on the shape of the density of states (DOS). By analogy with the calculated electronic structure of CaSi₂ with the AlB₂-type structure [18, 19], the $N(E_{\rm F})$ of $M_{\rm AE}(M_{\rm II0.5}, Si_{0.5})_2$ consists of mixed states of d states of the element $M_{\rm AE}$ and p states of the element M_{II} and Si. The d states are expected to shift upwards when the element M_{AE} is changed in the sequence Ca, Sr, and Ba. The upward shift of the d states changes the shape of DOS. Therefore, the change of the element MAE causes the shift of the Fermi energy, the change of the DOS shape, and, consequently, the change of $N(E_{\rm F})$. This would be reflected on the difference in the $T_{\rm C}$ among $M_{\rm AE}(M_{\rm II\,0.5}, Si_{0.5})_2$ with the same third element M_{II}.

In summary, the ternary silicides $M_I(M_{II0.5}, Si_{0.5})_2$ were found to be superconductors with the AlB₂-type structure, except for Ba(Al_{0.5}, Si_{0.5})₂. Therefore, silicides with the AlB₂type structure in M_{AE} - M_{II} -Si systems are concluded to be superconductive, except for that in the Ba-Al-Si system. On the other hand, in the binary alkaline-earth metal-boron system, only Mg forms a diboride with the AlB₂-type structure. In this sence, these ternary systems are in contrast with the binary alkaline-earth metal-boron system: the ternary alkaline-earth silicides have wider variations of the compounds with the AlB₂-typestructure than the binary alkaline-earth metal diborides.

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Sample	M _I (at. %)	M _{II} (at. %)	Si (at. %)	Phase
ARC-SrAl	31.8	33.0	35.2	$Sr(Al_{0.5}Si_{0.5})_2$
ARC-SrGa	33.8	33.2	33.0	$Sr(Ga_{0.5}Si_{0.5})_2$
ARC-BaAl	32.7	33.3	34.0	$Ba(Al_{0.5}Si_{0.5})_2$
ARC-BaGa ^{a)}	33.4	33.8	30.9	$Ba(Ga_{0.5}Si_{0.5})_2$

Table I. Chemical compositions of the main phase in the samples.

a) 1.8 at.% oxygen was detected in ARC-BaGa.

Phase	a(Å)	c(Å)	Volume (Å ³)	Theoretical density (gcm ⁻³)
$Ca(Al_{0.5}Si_{0.5})_2^{a)}$	4.1905(5)	4.3992(8)	66.90	2.37
$Sr(Al_{0.5}Si_{0.5})_2$	4.2475(3)	4.7421(6)	74.09	3.14
$Ba(Al_{0.5}Si_{0.5})_2$	4.2973(8)	5.1424(17)	82.24	3.84
$Ca(Ga_{0.5}Si_{0.5})_2^{b)}$	4.1200(8)	4.4401(1)	65.27	3.43
$Sr(Ga_{0.5}Si_{0.5})_2$	4.1875(4)	4.7447(4)	72.05	4.29
$Ba(Ga_{0.5}Si_{0.5})_2$	4.2587(4)	5.1039(9)	80.17	4.85

Table II. Lattice constants and theoretical density of $M_I(M_{II0.5}Si_{0.5})_2$ phases, together with those of $Ca(Al_{0.5}, Si_{0.5})_2$ and $Ca(Ga_{0.5}, Si_{0.5})_2$ phases.

a) Reference 12.

b) Reference 11.

Table III. Parameters of silicides $M_{AE}(M_{IIx}, Si_{1-x})_2$ (M_{AE} =Ca, Sr, and Ba, M_{II} =Al and Ga) observed in electrical resistivity and magnetization measurements. Units used in the magnetic shielding fraction and flux exclusion are a percentage of the theoretical value of the perfect diamagnetism (1/4 π).

Silicide	$T_{\rm C}^{\rm ONSET}$ (K)	$T_{\rm C}^{\rm ZERO}$ (K)	$T_{\rm C}^{\rm MEIS}$ (K)	Magnetic shielding	Flux exclusion in
				fraction in ZFC at	FC at 2 K (%)
				2 K (%)	
$Ca(Al_{0.5}, Si_{0.5})_2^{a)}$	8.0	7.7	7.7	60	7
$Sr(Al_{0.5}, Si_{0.5})_2$	4.3	4.2	4.2	>90	8
$Ca(Ga_{0.5}, Si_{0.5})_2^{b)}$	4.5	3.3	4.3	90	3
$Ca(Ga_{0.37}, Si_{0.63})_2^{b)}$	3.6	3.5	3.5	80	0.6
$Sr(Ga_{0.5}, Si_{0.5})_2$	5.2	5.1	5.1	90	8
$Sr(Ga_{0.37}, Si_{0.63})_2^{b)}$	4.7	3.6	4.2	90	4
$Sr(Ga_{0.37}, Si_{0.63})_2^{c)}$	3.5	3.4	3.4	80	8
Ba(Ga _{0.50} , Si _{0.50}) ₂	4.1	3.3	3.9	90	8
$Ba(Ga_{0.39}, Si_{0.61})_2^{b)}$	4.3	3.9	4.0	>90	6

a) Reference 12.

b) Reference 11.

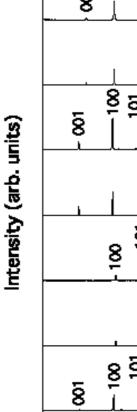
c) Reference 10.

Fig. 1. Powder X-ray diffraction patterns of $M_I(M_{II0.5}, Si_{0.5})_2$ (M_I =Sr and Ba, M_{II} =Al and Ga).

Fig. 2. Electrical resistivity of $M_I(Al_{0.5}, Si_{0.5})_2$ (M_I =Sr and Ba) as a function of the temperature.

Fig. 3. Electrical resistivity of $M_I(Ga_{0.5}, Si_{0.5})_2$ (M_I =Sr and Ba) as a function of the temperature.

Fig. 4. dc magnetization M of Sr(Al_{0.5}, Si_{0.5})₂, Sr(Ga_{0.5}, Si_{0.5})₂, and Ba(Ga_{0.5}, Si_{0.5})₂ measured in field H as a function of the temperature. The abbreviations "ZFC" and "FC" represent the magnetization measured in zero-field cooling and field cooling, respectively.



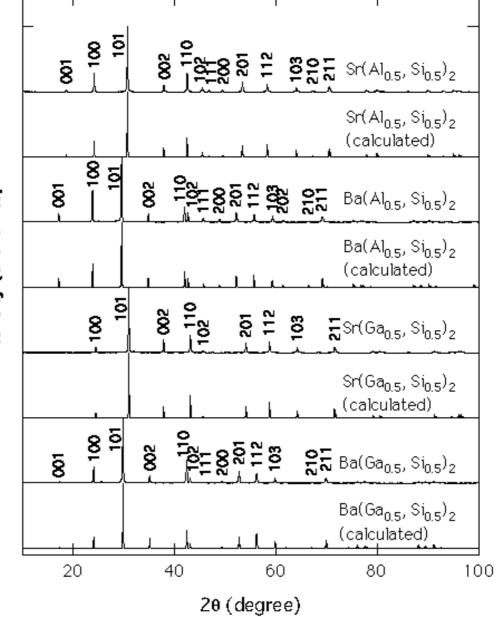


Fig.1 M. Imai et al.

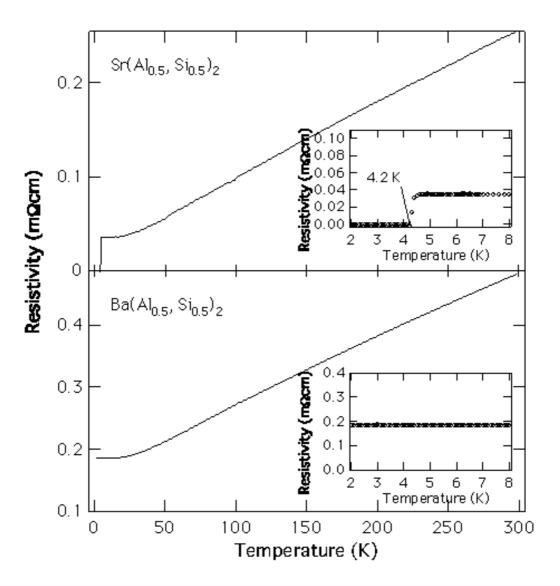


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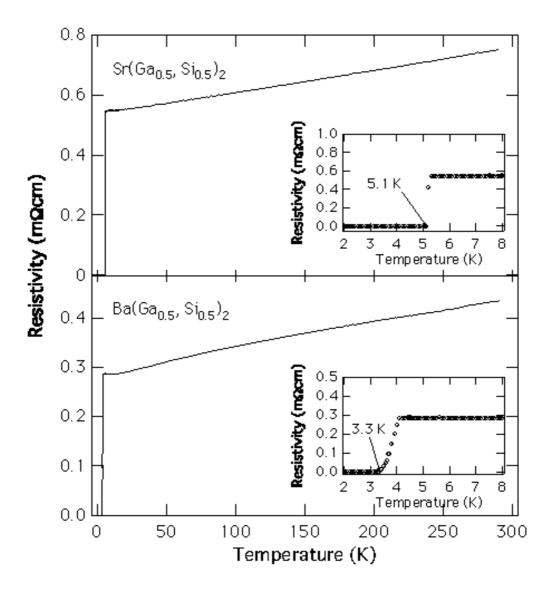


Fig.3 M. Imai et al.

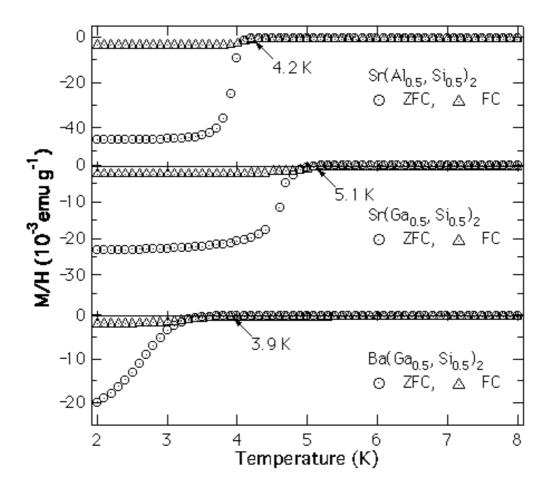


Fig. 4 M. Imai et al.